

ABSTRACT OF THE DISCLOSURE

An electrophotographic photoreceptor having an interlayer and a photosensitive layer on an electroconductive substrate, wherein the interlayer comprises any one of 1) an N-type semiconductive particle containing at least one of transition metals having an atomic number of 21 to 30, 39, 41 to 48 and 57 to 80, the total amount of the transition metals having an atomic number of 21 to 30, 39, 41 to 48 and 57 to 80 being from 100 ppm to 2.0% by mass, or 2) a metal oxide particle containing a silicon atom in a bond energy spectrum by the X-ray photoelectron spectroscopy at a ratio represented by the following Formula (1): Formula (1) $0.02 \leq \text{Si}/\text{M} \leq 0.55$ Si: a peak intensity of a silicon atom among the bond energy spectrum, and M: a peak intensity of a metal atom among the bond energy spectrum.